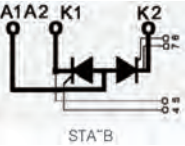
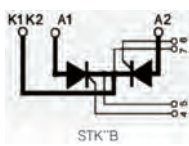
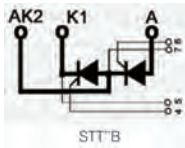


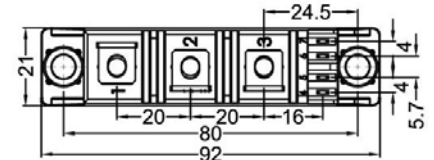
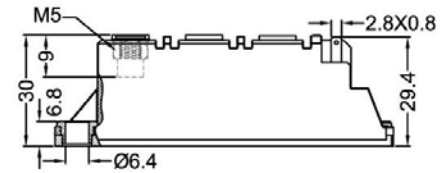
# STT100GKXXB

## Thyristor-Thyristor Modules



Type	V <sub>RSM</sub> V <sub>DSM</sub> V	V <sub>RRM</sub> V <sub>DRM</sub> V
STT100GK08B	900	800
STT100GK12B	1300	1200
STT100GK14B	1500	1400
STT100GK16B	1700	1600
STT100GK18B	1900	1800
STT100GK20B	2100	2000
STT100GK22B	2300	2200

Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions	Maximum Ratings	Unit
I <sub>TRMS</sub> , I <sub>FRMS</sub> I <sub>TAVM</sub> , I <sub>FAVM</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> T <sub>C</sub> =85°C; 180° sine	180 100	A
I <sub>TSM</sub> , I <sub>FSM</sub>	T <sub>VJ</sub> =45°C V <sub>R</sub> =0 t=10ms (50Hz), sine t=8.3ms (60Hz), sine	1700 1800	A
	T <sub>VJ</sub> =T <sub>VJM</sub> V <sub>R</sub> =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine	1540 1640	
∫i <sup>2</sup> dt	T <sub>VJ</sub> =45°C V <sub>R</sub> =0 t=10ms (50Hz), sine t=8.3ms (60Hz), sine	14450 13500	A <sup>2</sup> s
	T <sub>VJ</sub> =T <sub>VJM</sub> V <sub>R</sub> =0 t=10ms(50Hz), sine t=8.3ms(60Hz), sine	11850 11300	
(di/dt) <sub>cr</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> f=50Hz, t <sub>p</sub> =200us V <sub>D</sub> =2/3V <sub>DRM</sub> I <sub>G</sub> =0.45A di <sub>G</sub> /dt=0.45A/us repetitive, I <sub>T</sub> =250A	150	A/us
	non repetitive, I <sub>T</sub> =I <sub>TAVM</sub>	500	
(dv/dt) <sub>cr</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> ; R <sub>GK</sub> =∞; method 1 (linear voltage rise) V <sub>DR</sub> =2/3V <sub>DRM</sub>	1000	V/us
P <sub>GM</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> I <sub>T</sub> =I <sub>TAVM</sub> t <sub>p</sub> =30us	10	W
	t <sub>p</sub> =300us	5	
P <sub>GAV</sub>		0.5	W
V <sub>RGM</sub>		10	V
T <sub>VJ</sub> T <sub>VJM</sub> T <sub>stg</sub>		-40...+125	°C
		125	
		-40...+125	
V <sub>ISOL</sub>	50/60Hz, RMS I <sub>ISOL</sub> ≤1mA t=1min	3000	V~
	t=1s	3600	
M <sub>d</sub>	Mounting torque (M5)	2.5-4.0/22-35	Nm/lb.in.
	Terminal connection torque (M5)	2.5-4.0/22-35	
Weight	Typical	110	g



# STT100GKXXB

## Thyristor-Thyristor Modules

Symbol	Test Conditions	Characteristic Values	Unit
$I_{RRM}, I_{DRM}$	$T_{VJ}=T_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	15	mA
$V_T, V_F$	$I_T, I_F=300A; T_{VJ}=25^{\circ}C$	1.74	V
$V_{TO}$	For power-loss calculations only ( $T_{VJ}=T_{VJM}$ )	0.85	V
$r_T$		3.2	m $\Omega$
$V_{GT}$	$V_D=6V;$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	1.5 1.6	V
$I_{GT}$	$V_D=6V;$ $T_{VJ}=25^{\circ}C$ $T_{VJ}=-40^{\circ}C$	100 200	mA
$V_{GD}$	$T_{VJ}=T_{VJM};$ $V_D=2/3V_{DRM}$	0.25	V
$I_{GD}$	$T_{VJ}=T_{VJM};$ $V_D=2/3V_{DRM}$	10	mA
$I_L$	$T_{VJ}=25^{\circ}C; t_p=30\mu s; V_D=6V$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	200	mA
$I_H$	$T_{VJ}=25^{\circ}C; V_D=6V; R_{GK}=\infty$	150	mA
$t_{gd}$	$T_{VJ}=25^{\circ}C; V_D=1/2V_{DRM}$ $I_G=0.45A; di_G/dt=0.45A/\mu s$	2	$\mu s$
$t_q$	$T_{VJ}=T_{VJM}; I_T=150A; t_p=200\mu s; -di/dt=10A/\mu s$ $V_R=100V; dv/dt=20V/\mu s; V_D=2/3V_{DRM}$	typ. 185	$\mu s$
$Q_S$	$T_{VJ}=T_{VJM}; I_T, I_F=50A; -di/dt=6A/\mu s$	170	$\mu C$
$I_{RM}$		45	A
$R_{thJC}$	per thyristor/diode; DC current per module	0.22 0.11	K/W
$R_{thJK}$	per thyristor/diode; DC current per module	0.42 0.21	K/W
$d_s$	Creeping distance on surface	12.7	mm
$d_A$	Creepage distance in air	9.6	mm
$a$	Maximum allowable acceleration	50	m/s <sup>2</sup>

### FEATURES

- \* International standard package
- \* Copper base plate
- \* Glass passivated chips
- \* Isolation voltage 3600 V~
- \* UL file NO.E310749
- \* RoHS compliant

### APPLICATIONS

- \* DC motor control
- \* Softstart AC motor controller
- \* Light, heat and temperature control

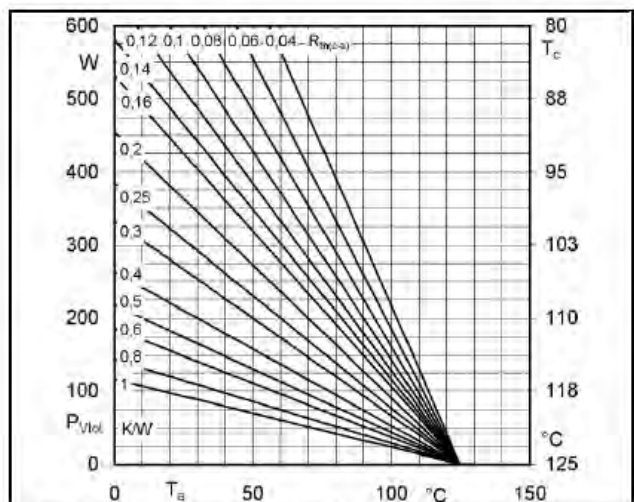
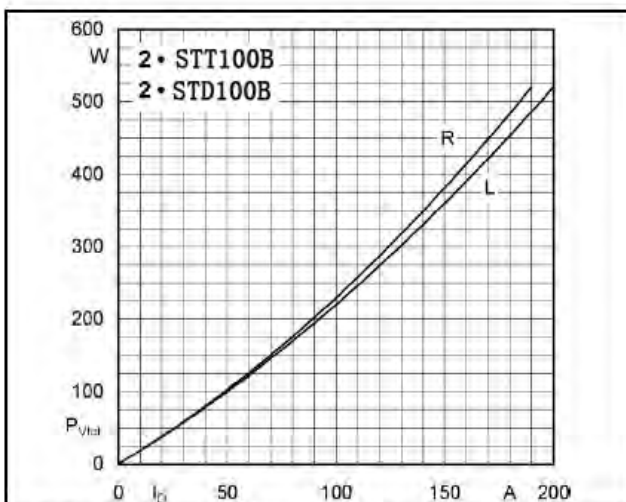
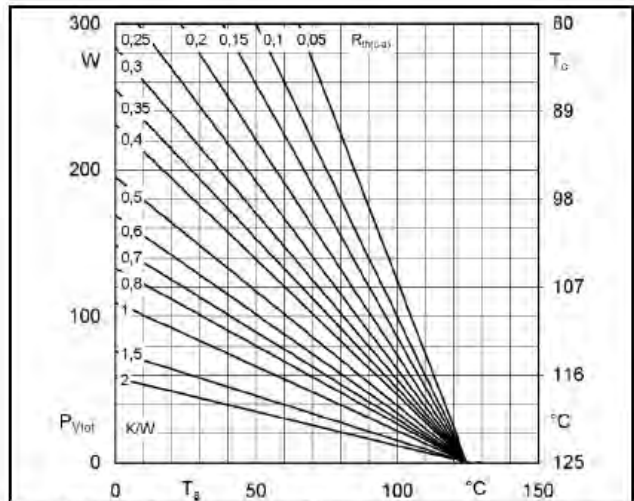
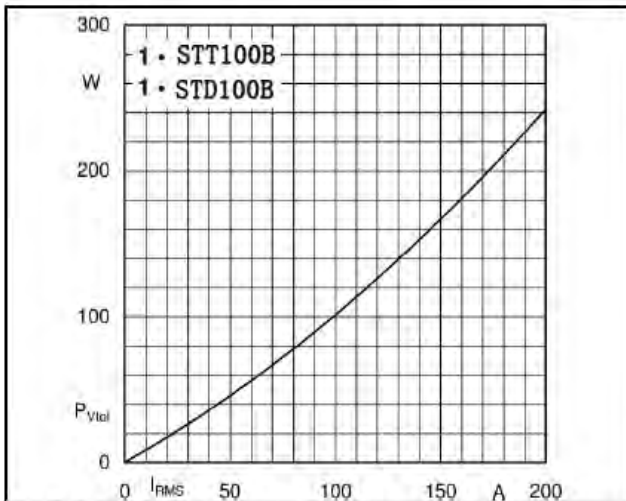
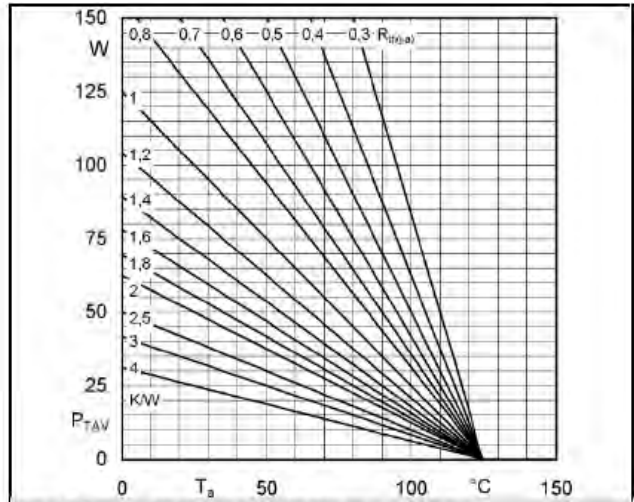
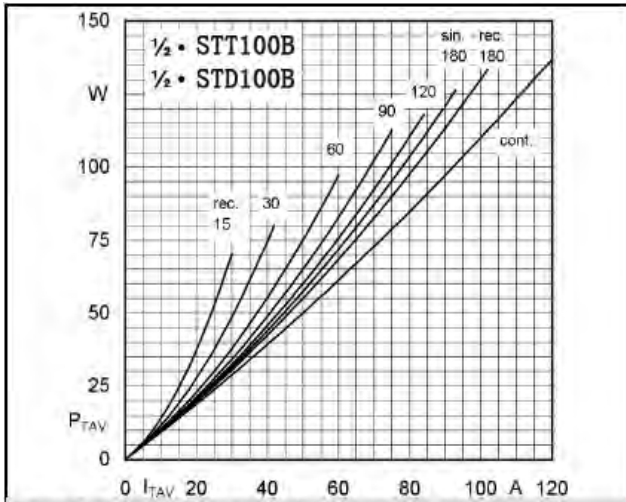
### ADVANTAGES

- \* Space and weight savings
- \* Simple mounting with two screws
- \* Improved temperature and power cycling
- \* Reduced protection circuits



# STT100GKXXB

## Thyristor-Thyristor Modules





# STT100GKXXB

## Thyristor-Thyristor Modules

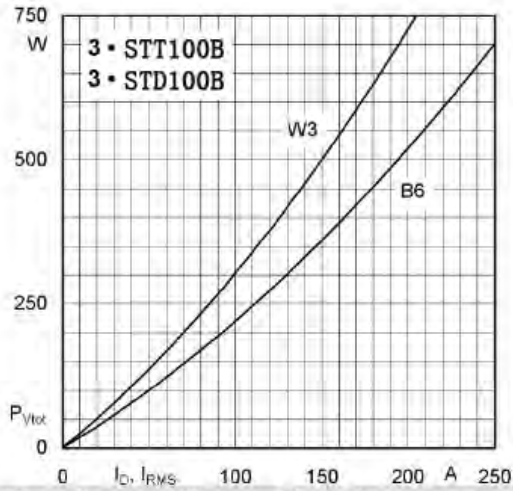


Fig. 4L Power dissipation of three modules vs. direct and rms current

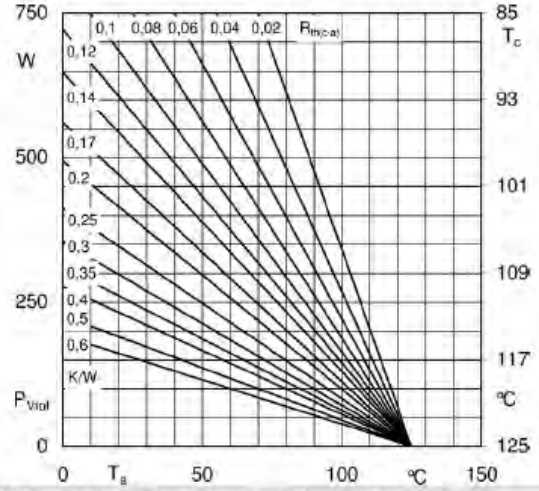


Fig. 4R Power dissipation of three modules vs. case temp.

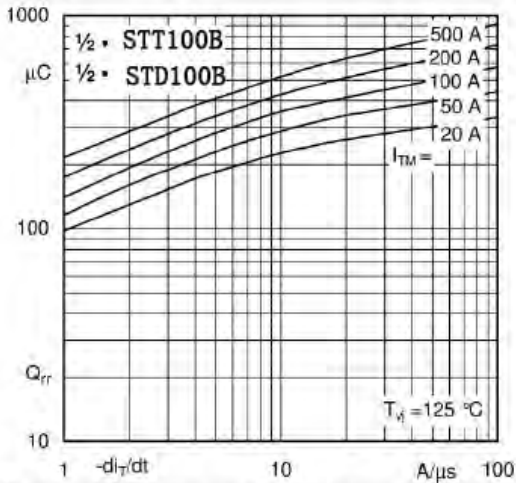


Fig. 5 Recovered charge vs. current decrease

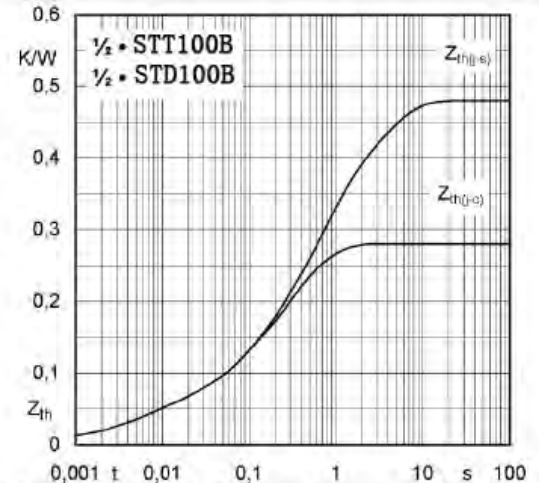


Fig. 6 Transient thermal impedance vs. time

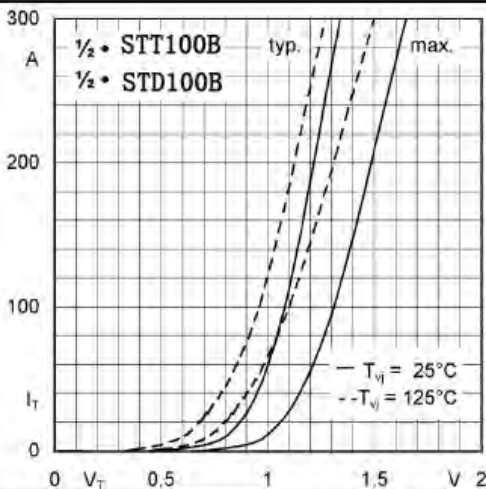


Fig. 7 On-state characteristics

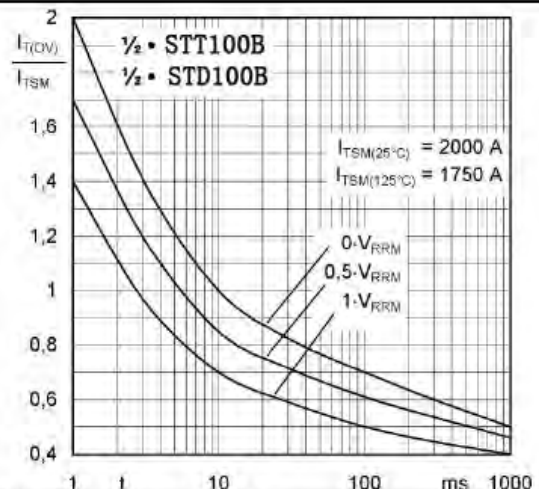


Fig. 8 Surge overload current vs. time